

600V N-Channel MOSFET

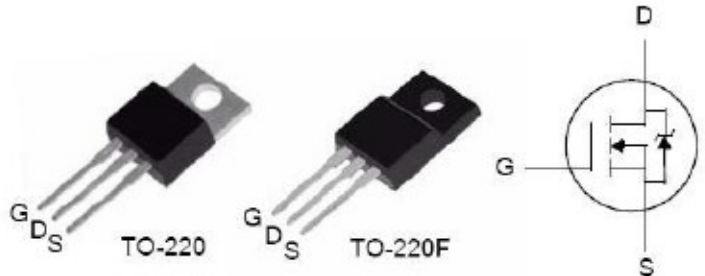
General Features

- Low ON Resistance
- Low Gate Charge (typical 14.7nC)
- Fast Switching
- 100% Avalanche Tested
- RoHS Compliant
- Halogen-free available

BV_{DSS}	$R_{DS(ON)}$ (Max.)	I_D
600V	2.8 Ω	3.6A

Applications

- High Efficiency SMPS
- Adaptor/Charger
- Active PFC
- LCD Panel Power



Ordering Information

Part Number	Package	MDSing	RemDS
FTP04N60B	TO-220	FTP04N60B	RoHS
FTP04N60BG	TO-220	FTP04N60BG	Halogen-free
FTA04N60B	TO-220F	FTA04N60B	RoHS
FTA04N60BG	TO-220F	FTA04N60BG	Halogen-free

Absolute Maximum Ratings

$T_c=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	FTP04N60B	FTA04N60B	Unit
V_{DSS}	Drain-to-Source Voltage ^[1]	600		V
I_D	Continuous Drain Current	3.6	3.6*	A
$I_{D@100^\circ\text{C}}$	Continuous Drain Current	Figure 3		
I_{DM}	Pulsed Drain Current, $V_{GS}@10\text{V}$ ^[2]	Figure 6		
P_D	Power Dissipation	89	22	W
	Derating Factor above 25 $^\circ\text{C}$	0.71	0.18	W/ $^\circ\text{C}$
V_{GS}	Gate-to-Source Voltage	± 30		V
E_{AS}	Single Pulse Avalanche Energy $L=24\text{mH}$, $I_D=3.4\text{A}$	140		mJ
dv/dt	Peak Diode Recovery dv/dt ^[3]	4.5		V/ns
T_L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300		$^\circ\text{C}$
T_J and T_{STG}	Operating and Storage Temperature Range	-55 to 150		

*Drain Current limited by Maximum Junction Temperature.

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	FTP04N60B	FTA04N60B	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.4	5.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	60	60	

Electrical Characteristics

OFF Characteristics

$T_c=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	600	--	--	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	--	0.6	--	V/°C	Reference to 25°C, $I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	20	μA	$V_{DS}=600V, V_{GS}=0V$
		--	--	100		$V_{DS}=480V, V_{GS}=0V,$ $T_c=125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	100	nA	$V_{GS}=+30V$
		--	--	-100		$V_{GS}=-30V$

ON Characteristics

$T_c=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	2.4	2.8	Ω	$V_{GS}=10V, I_D=1.8A_{[4]}$
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
gfs	Forward Transconductance	--	2.85	--	S	$V_{DS}=15V, I_D=3.6A_{[4]}$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{ISS}	Input Capacitance	--	498	--	pF	$V_{GS}=0V$ $V_{DS}=25V$ $f=1.0MHz$ Figure 14
C_{OSS}	Output Capacitance	--	39	--		
C_{RSS}	Reverse Transfer Capacitance	--	7.5	--		
Q_G	Total Gate Charge	--	14.7	--	nC	$V_{DD}=300V$ $I_D=3.6A$ Figure 15
Q_{GS}	Gate-to-Source Charge	--	2.1	--		
Q_{GD}	Gate-to-Drain (Miller) Charge	--	7.0	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	14	--	ns	$V_{DD}=300V$ $I_D=3.6A$ $V_{GS}=10V$ $R_G=20\Omega$
t_{rise}	Rise Time	--	33	--		
$t_{d(OFF)}$	Turn-off Delay Time	--	34	--		
t_{fall}	Fall Time	--	31	--		

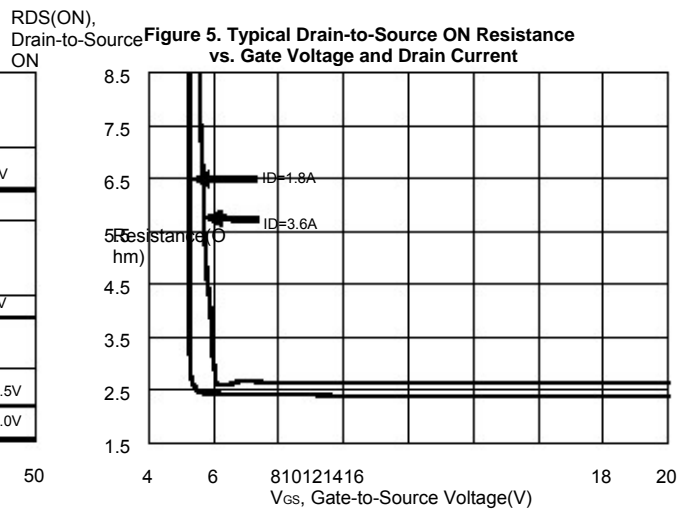
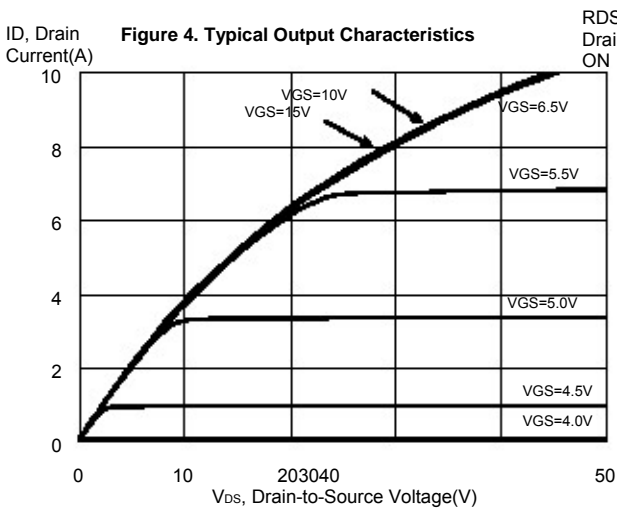
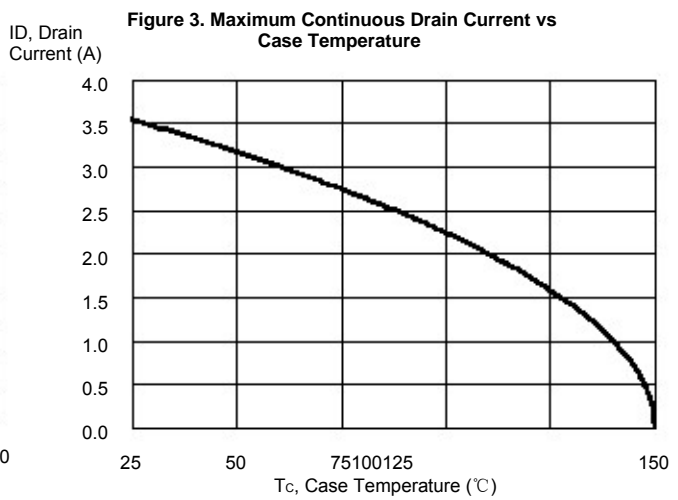
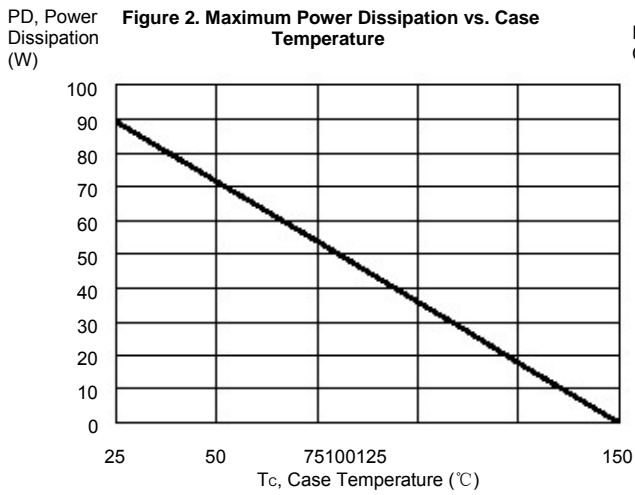
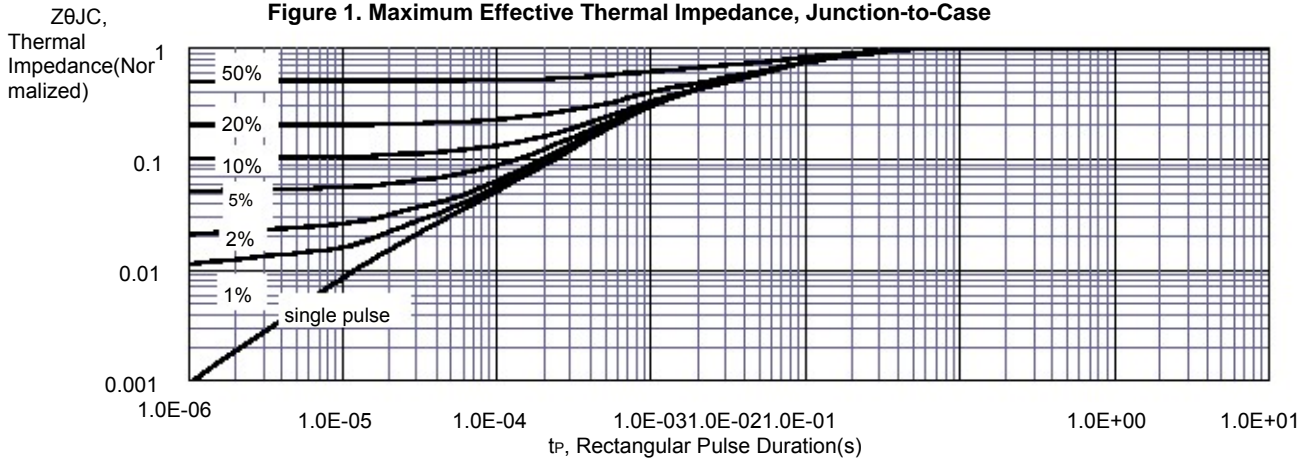
Source-Drain Diode Characteristics

Tc=25°C unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Units	Test Conditions
I _{SD}	Continuous Source Current (Body Diode)	--	--	3.6	A	Integral P-N diode in MOSFET
I _{SM}	Maximum Pulsed Current(Body Diode)	--	--	14.4	A	
V _{SD}	Diode Forward Voltage	--	--	1.2	V	I _S =3.6A, V _{GS} =0V
t _{rr}	Reverse Recovery Time	--	224	--	ns	V _{GS} =0V I _F =3.6A, di/dt=100A/μs
Q _{rr}	Reverse Recovery Charge	--	960	--	nC	

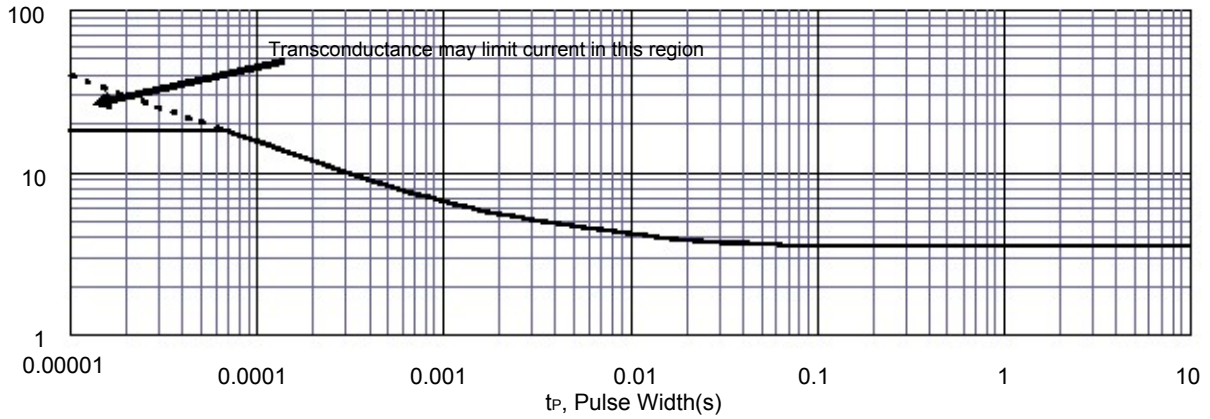
NOTE:

- [1] T_J=+25°C to +150°C
- [2] Repetitive rating, pulse width limited by maximum junction temperature.
- [3] I_{SD}=3.6A, di/dt≤100A/μs, V_{DD}≤B_VD_{SS}, T_J=+150°C
- [4] Pulse width≤380μs; duty cycle≤2%.



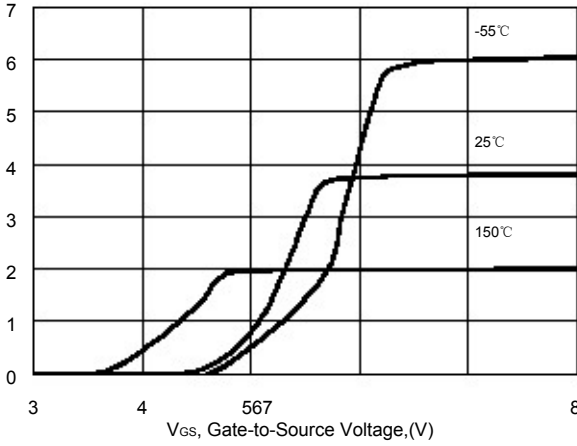
IDM, Peak Current(A)

Figure 6. Maximum Peak Current Capability



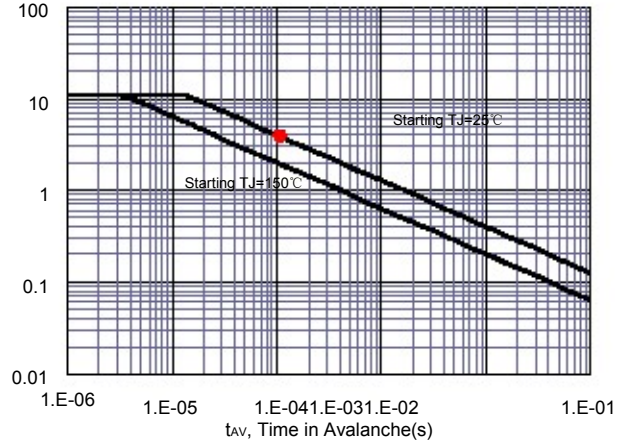
ID, Drain-to-Source Current (A)

Figure 7. Typical Transfer Characteristics



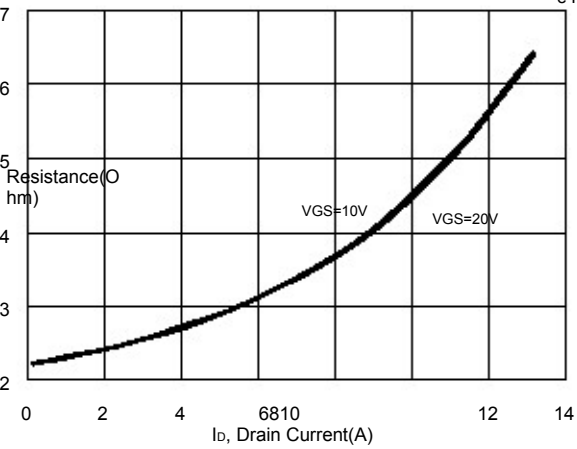
IAS, Avalanche Current(A)

Figure 8. Unclamped Inductive Switching Capability



RDS(ON), Drain-to-Source ON Resistance

Figure 9. Typical Drain-to-Source ON Resistance



RDS(ON), Drain-to-Source ON Resistance

Figure 10. Typical Drain-to-Source On Resistance vs. Junction Temperature

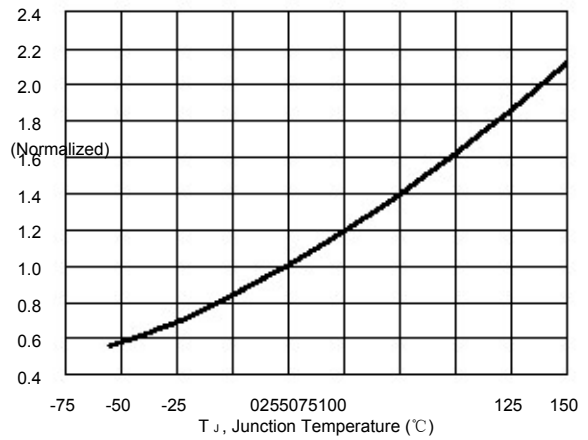


Figure 11. Typical Breakdown Voltage vs. Junction Temperature

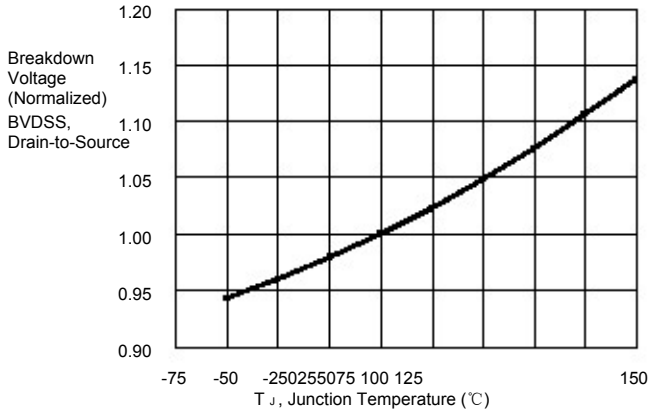


Figure 12. Typical Threshold Voltage vs. Junction Temperature

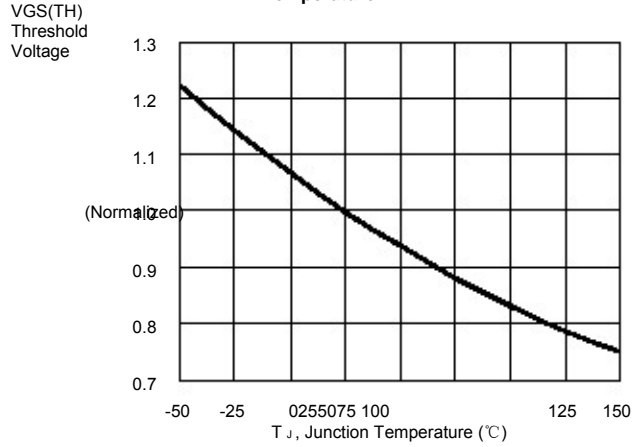


Figure 13. Maximum Forward Safe Operation Area

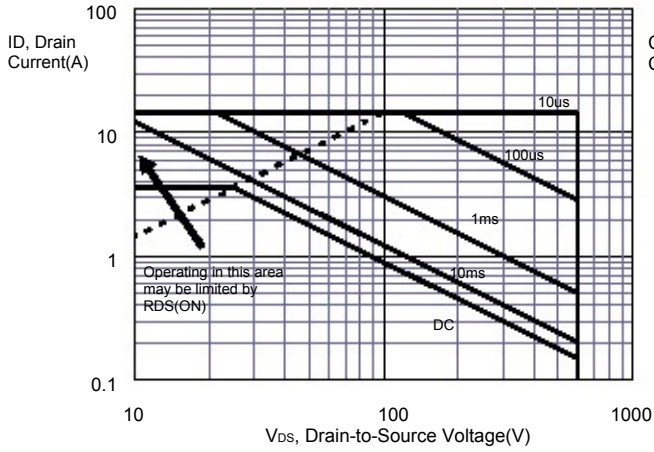


Figure 14. Typical Capacitance vs. Drain-to-Source Voltage

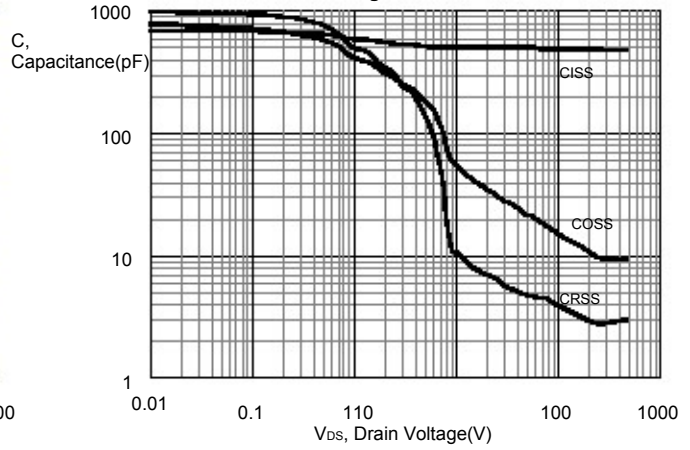


Figure 15. Typical Gate Charge vs. Gate-to-Source Voltage

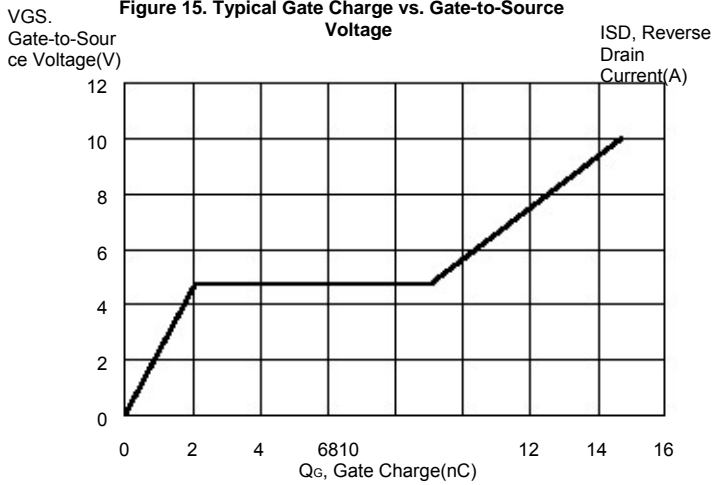
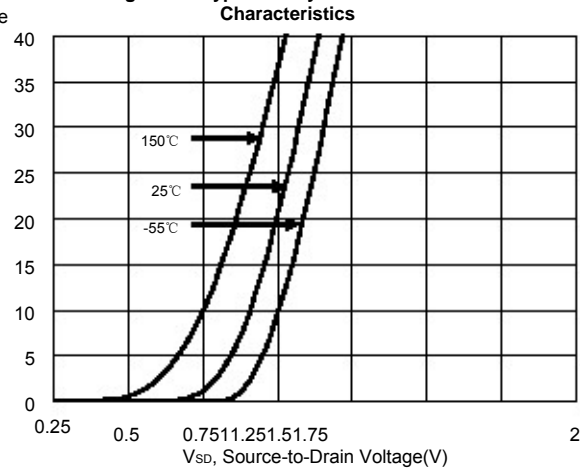


Figure 16. Typical Body Diode Transfer Characteristics



Test Circuit

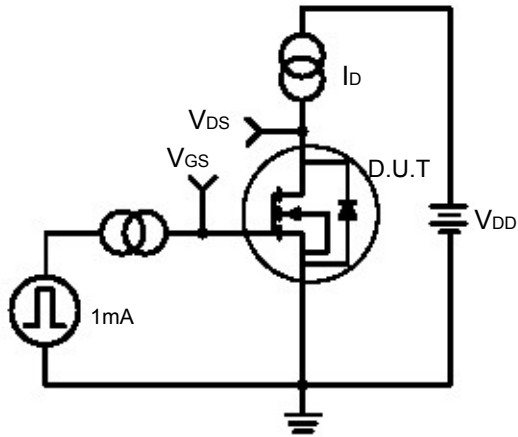


Figure 17. Gate Charge Test Circuit

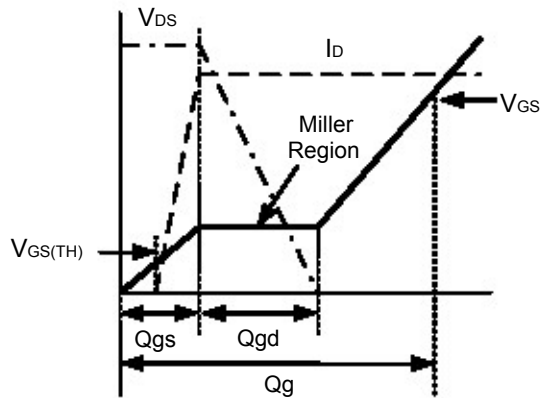


Figure 18. Gate Charge Waveform

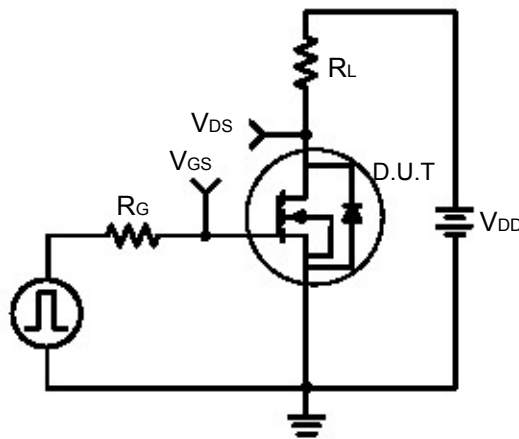


Figure 19. Resistive Switching Test Circuit

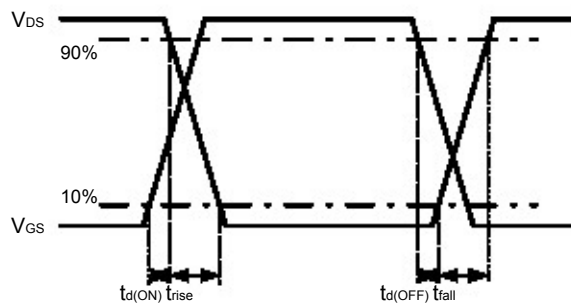


Figure 20. Resistive Switching Waveforms

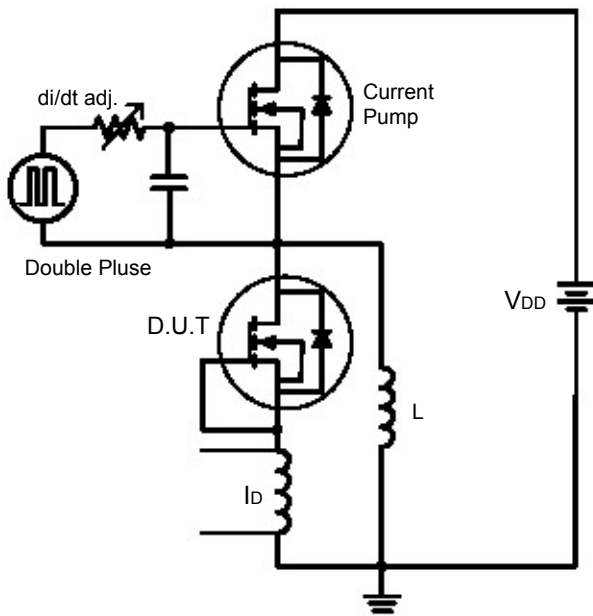


Figure 21. Diode Reverse Recovery Test Circuit

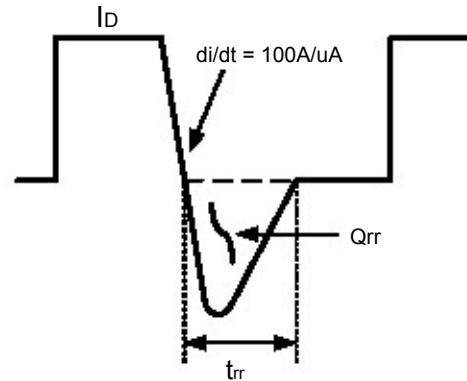


Figure 22. Diode Reverse Recovery Waveform

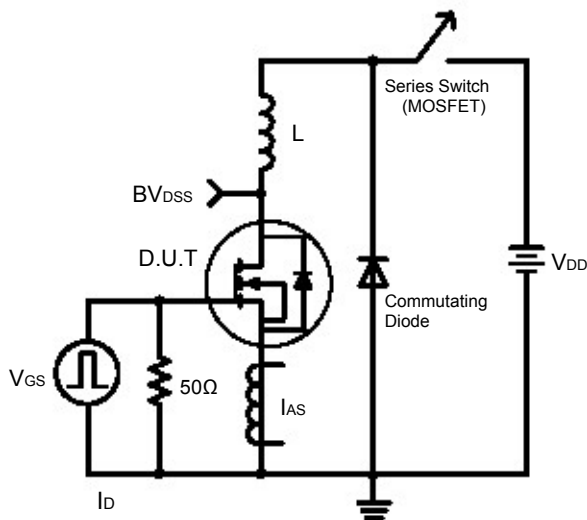


Figure 23. Unclamped Inductive Switching Test Circuit

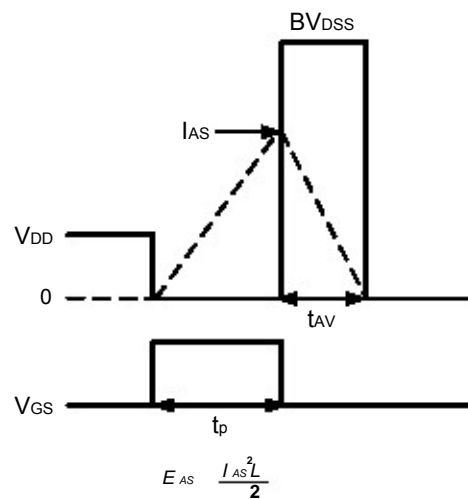
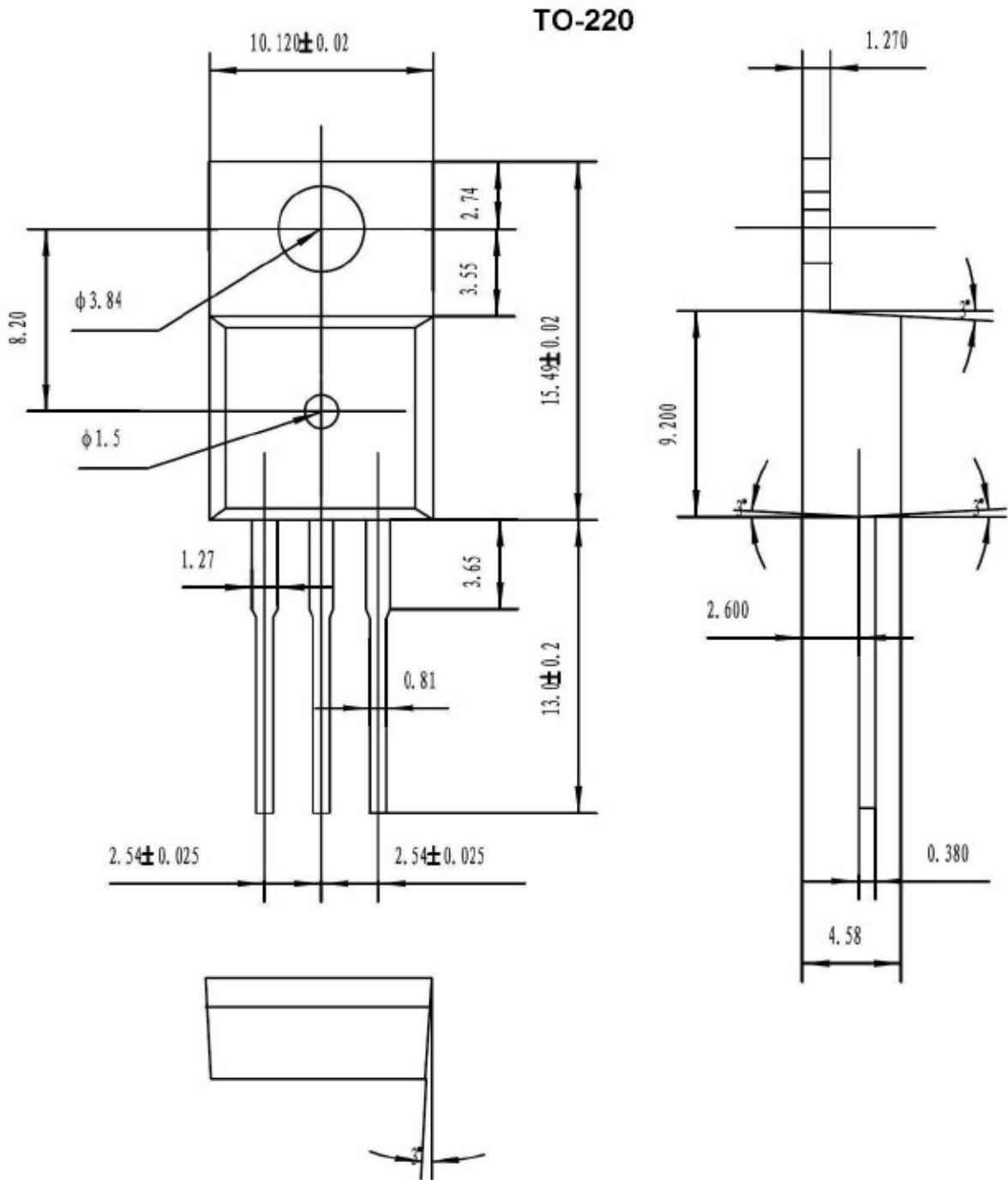


Figure 24. Unclamped Inductive Switching Waveforms

Package Dimensions



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